

Pyroelectric Response in $\text{Hf}_{1-x}\text{Zr}_x\text{O}_2$ Thin Films

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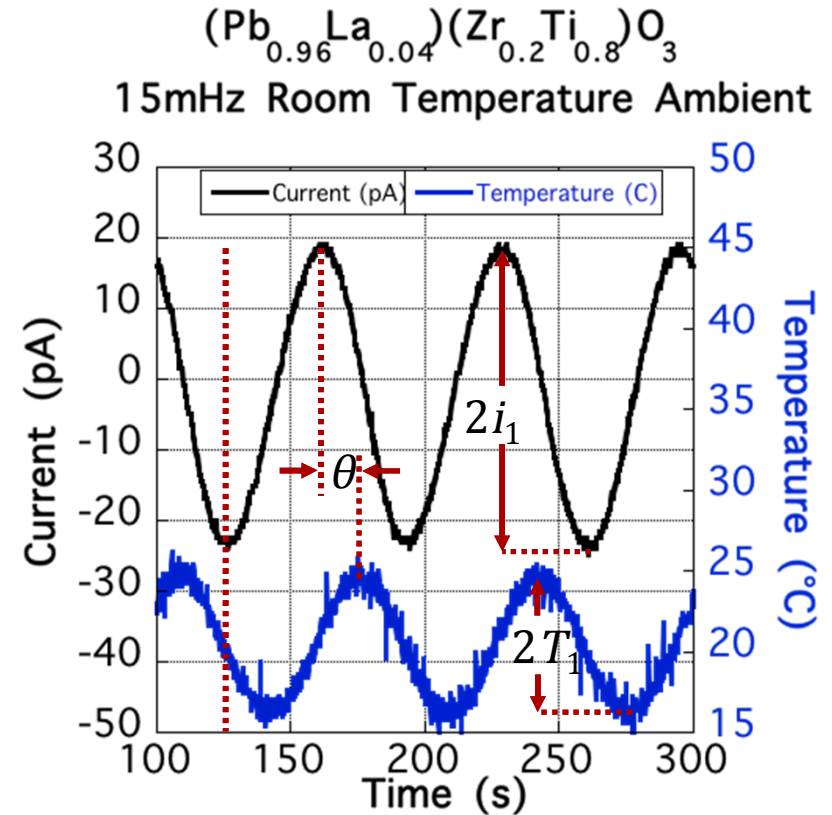
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Doped HfO₂ Pyroelectric Response

- Ferroelectric with permanent polarization must have a pyroelectric response
- Park *et al.* Nano Energy 2014
 - Hf_{1-x}Zr_xO₂ ($0.7 \leq X \leq 0.9$)
 - Measured Polarization-Electric field hysteresis curves at various Temperatures
- Hoffman *et al.* Nano Energy 2015
 - Si:HfO₂
 - Measured pyroelectric coefficient due to orthorhombic to tetragonal phase change
 - Pyroelectric current measured while sample temperature increased
- These methods can be influenced by extrinsic artifacts such as leakage current.

Pyroelectric Measurements

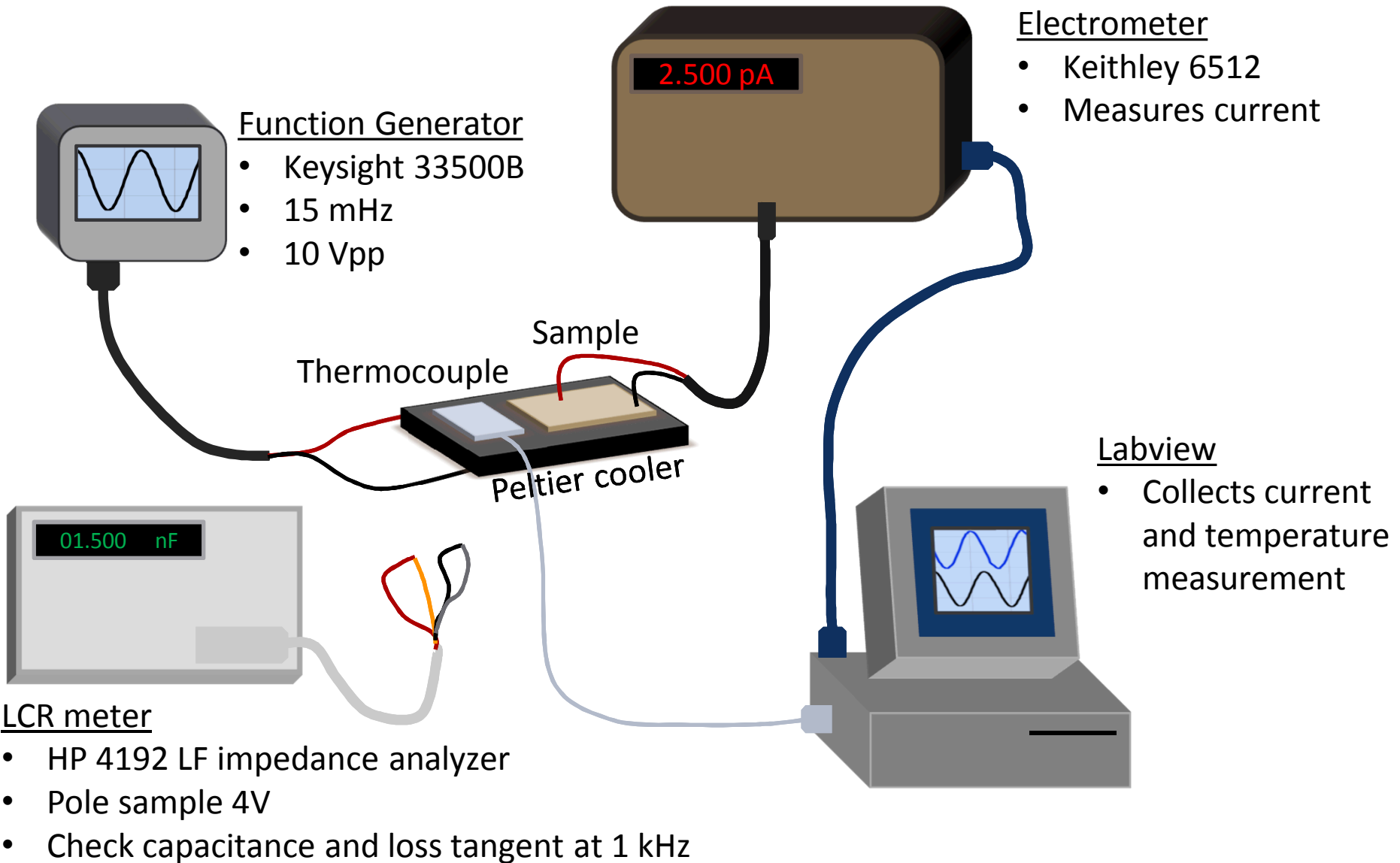
- Static
 - Charge compensation by leakage current
- Indirect
 - Incomplete switching or fatigue
- Dynamic
 - Linear temperature – (Byer-Roundy)
 - Difficult to separate pyroelectric and other thermally induced currents
 - Oscillating temperature
 - Peltier device small sinusoidal temperature waveform
 - Pyroelectric current is 90° out of phase with temperature waveform



$$i_1 \sin(\theta) = pA\omega T_1$$

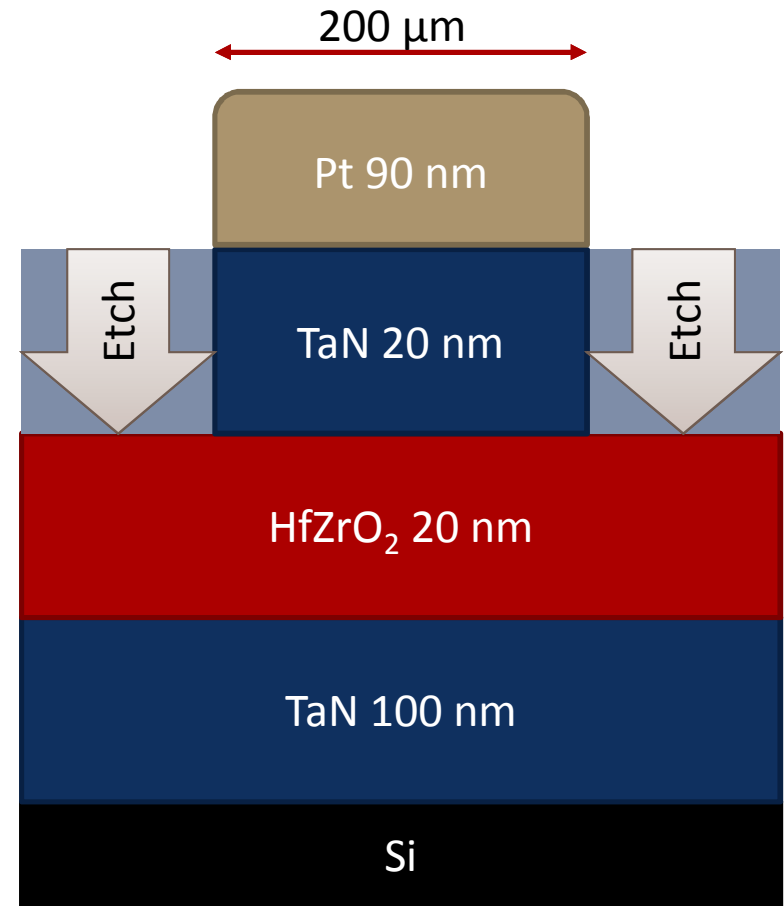
p – pyroelectric coefficient
 ω – angular frequency of temperature
 A – area of device

Pyroelectric Setup

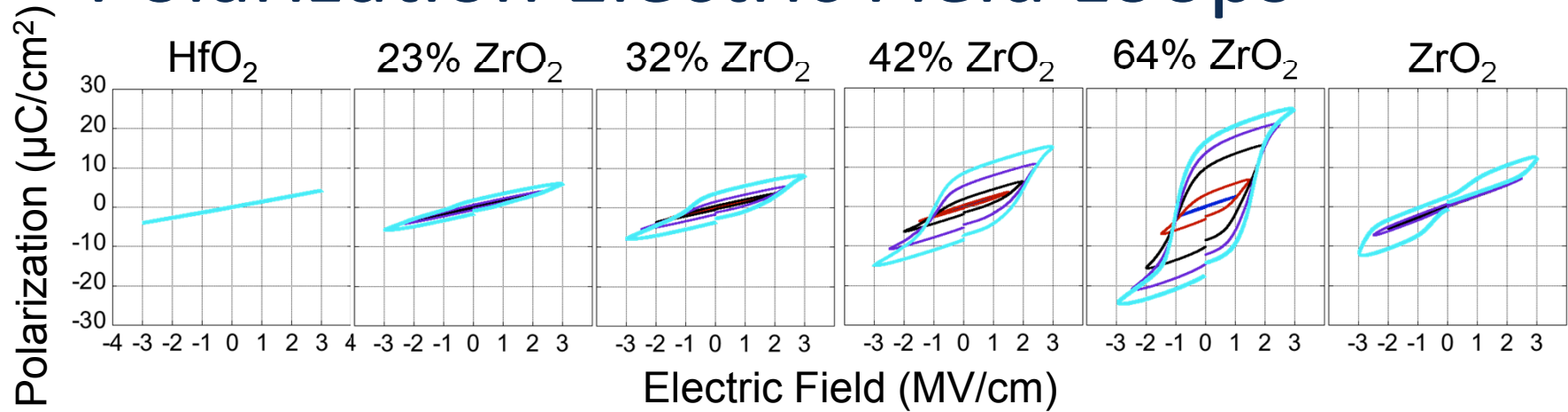


Experimental and Device Stack

- RF sputter TaN from TaN target
- Thermal ALD $\text{Hf}_{1-x}\text{Zr}_x\text{O}_2$ at 150 °C by TDMA Hf, TDMA Zr, and H_2O
 - Cycle ratio to control composition
- RF sputter blanket TaN cap
- Rapid thermal anneal 30s at 600 °C under nitrogen
- Sputter Pt through shadow-mask
- ICP reactive ion etch
 - SF_6 and C_4F_8 atmosphere

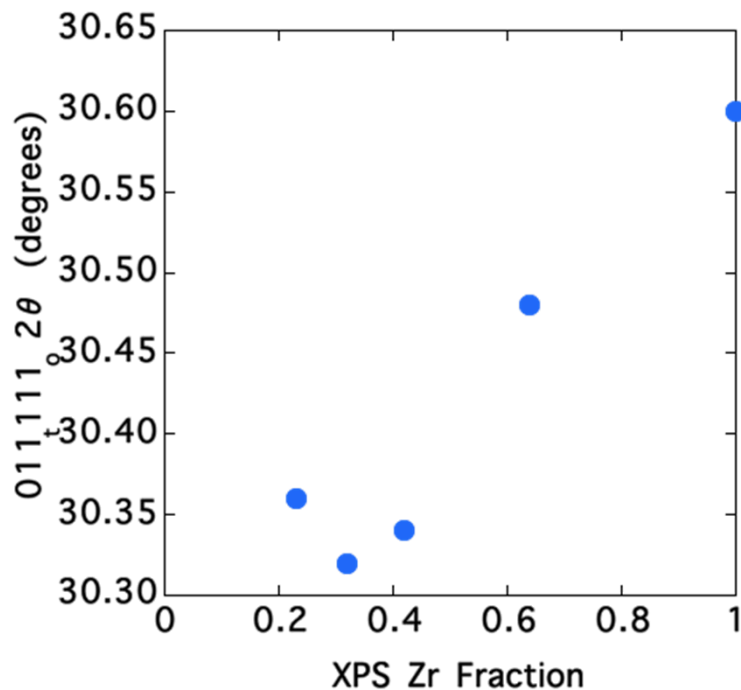
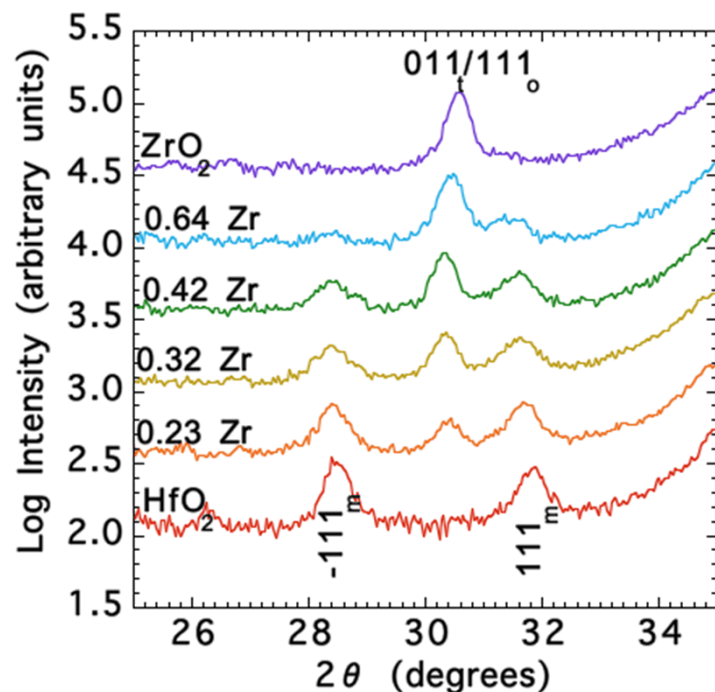


Polarization Electric Field Loops



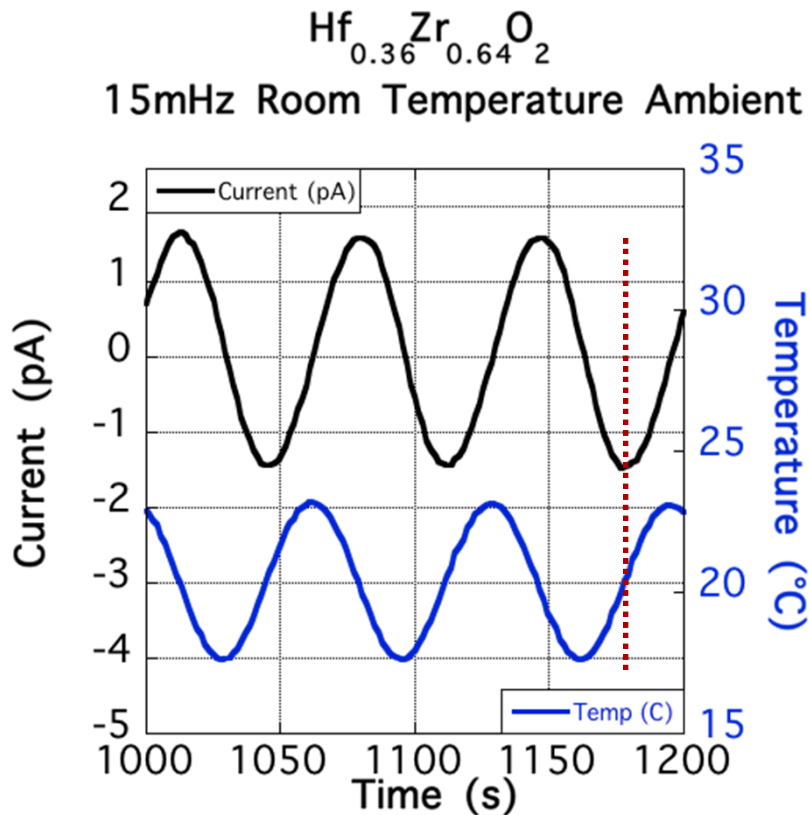
- Composition, measured by XPS, is HfO₂ rich as expected with larger HfO₂ growth per cycle.
- Trend similar to literature.
 - Antiferroelectric consistent with ZrO₂
- Remanent polarization does not saturate due to leakage current

Phase Assemblage

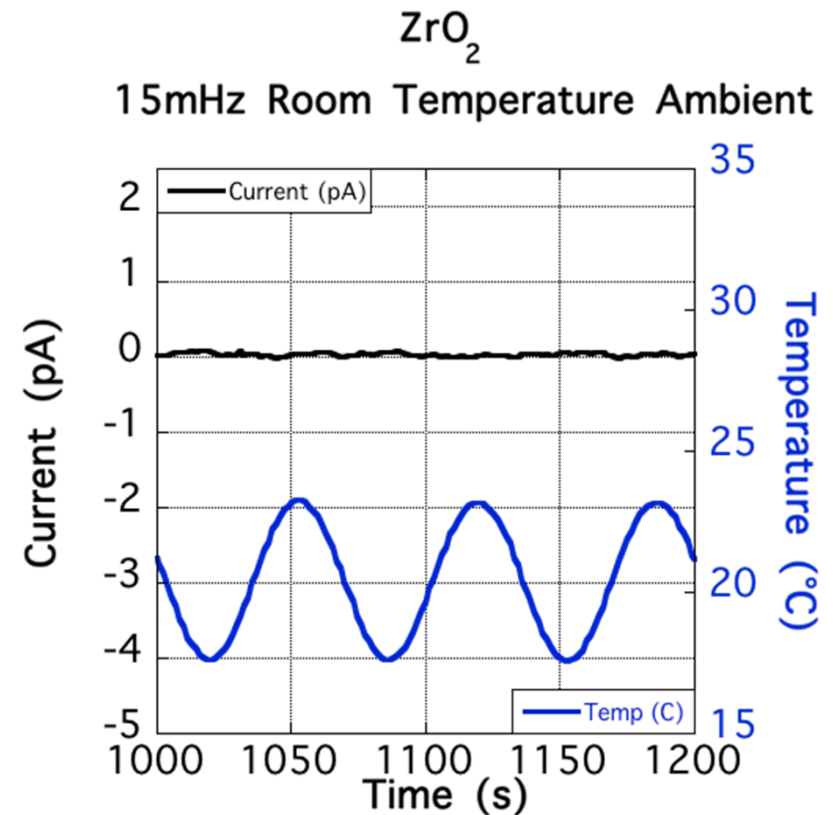


- Monoclinic peaks decrease and Orthorhombic/Tetragonal increase with increased Zr content
- $011t/111o$ peak shifts to higher angles with increased Zr content
- Orthorhombic/tetragonal intensity correlates with polarization response

Pyroelectric Waveforms

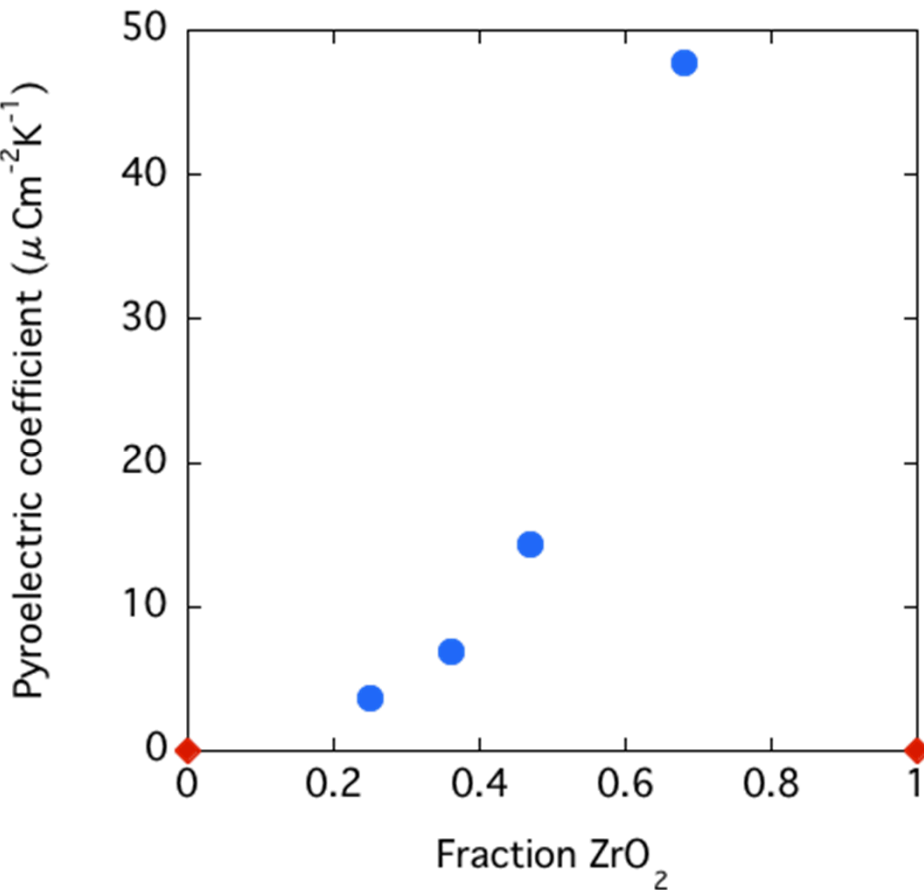


Pyroelectric current measurement for $\text{Hf}_{0.36}\text{Zr}_{0.64}\text{O}_2$ film.



Pyroelectric current measurement for ZrO_2 film.

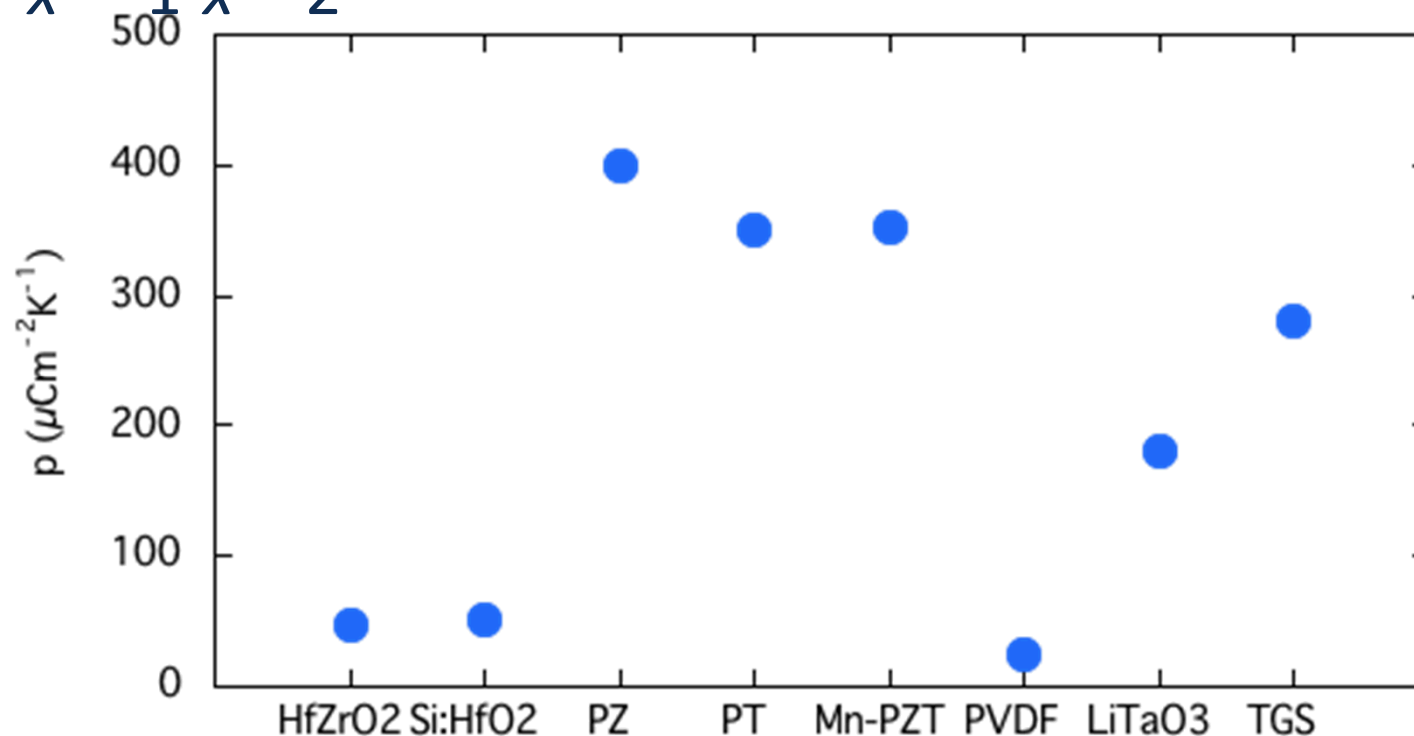
Pyroelectric Coefficients



Room temperature pyroelectric coefficient for $\text{Hf}_{1-x}\text{Zr}_x\text{O}_2$ films as a function of Zr content.

- Pure HfO_2 and ZrO_2 : no pyroelectric response
- Increasing pyroelectric coefficient with Zr content
 - Maximum: $48 \mu\text{Cm}^{-2}\text{K}^{-1}$ at 68% ZrO_2
- Follows polarization and orthorhombic phase content trend.

Hf_xZr_{1-x}O₂ & Other Materials



Material	p ($\mu\text{Cm}^{-2}\text{K}^{-1}$)	Dielectric properties		F_I 10^{-10} (mV^{-1})	F_V (m^2C^{-1})	F_D 10^{-6} ($\text{Pa}^{-1/2}$)	Reference
		ϵ	$\tan \delta$				
Hf _{0.32} Zr _{0.68} O ₂	48	25	0.014	0.22	0.10*	13*	This work
5.6 mol% Si:HfO ₂	52	38	0.025	0.20	0.06	7	Hoffmann 2015 Nano Energy
Mod. PZT	400	290	0.003	0.02	0.06	58	Whatmore 2004 J
Mod. PT	350	220	0.01	0.01	0.07	32	Electroceramics
Mn -PZT thin film	352	257	0.007	-	-	39	Sebald 2008 IEEE Trans.
PVDF	25	9	0.03	0.11	0.14	7	Ploss 1991 Sensors and Actuators A
LiTaO ₃	180	47	0.005	0.56	0.14	39	
TGS	280	38	0.01	1.2	0.36	66	

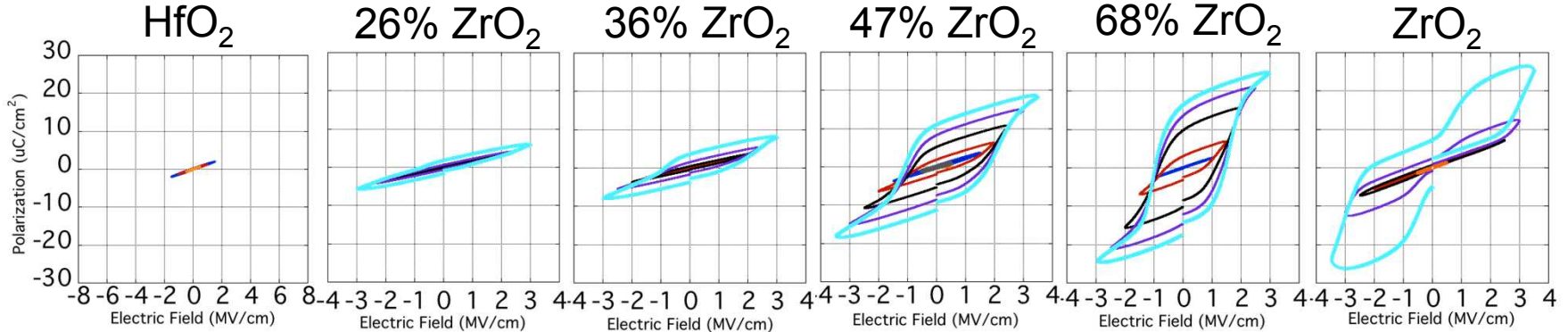
* Literature value bulk heat capacity

Conclusions

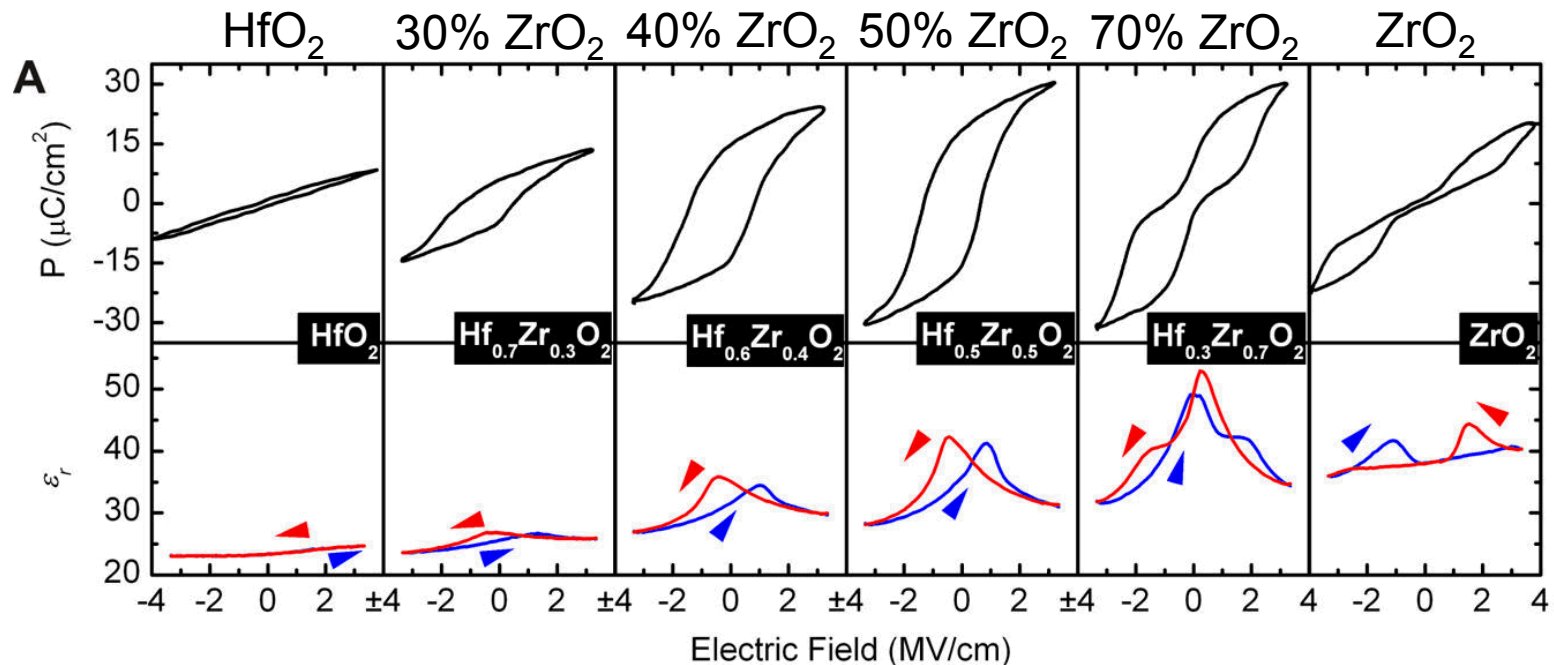
- We do observe a pyroelectric response in $\text{Hf}_{1-x}\text{Zr}_x\text{O}_2$
 - Consistent with permanent polarization
 - Consistent with ferroelectricity
- Pyroelectric response, polarization magnitude, orthorhombic/tetragonal phase fraction, are all correlated with Zr content.
- $\text{Hf}_{0.32}\text{Zr}_{0.68}\text{O}_2$ pyroelectric coefficient and IR detector figures of merit similar to PVDF and LiTaO_3
 - $p=48 \mu\text{Cm}^{-2}\text{K}^{-1}$
 - $F_I= 0.22 \text{ mV}^{-1}$
 - $F_V= 0.10 \text{ m}^2\text{C}^{-1}$
- This could be a promising material for large area IR detectors or low frequency detection.

BONUS SLIDES

Polarization electric field loops

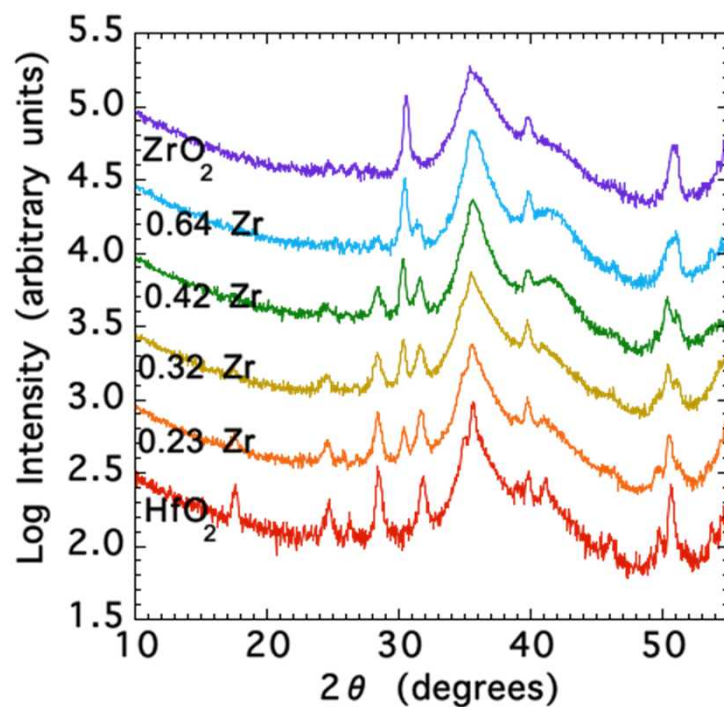
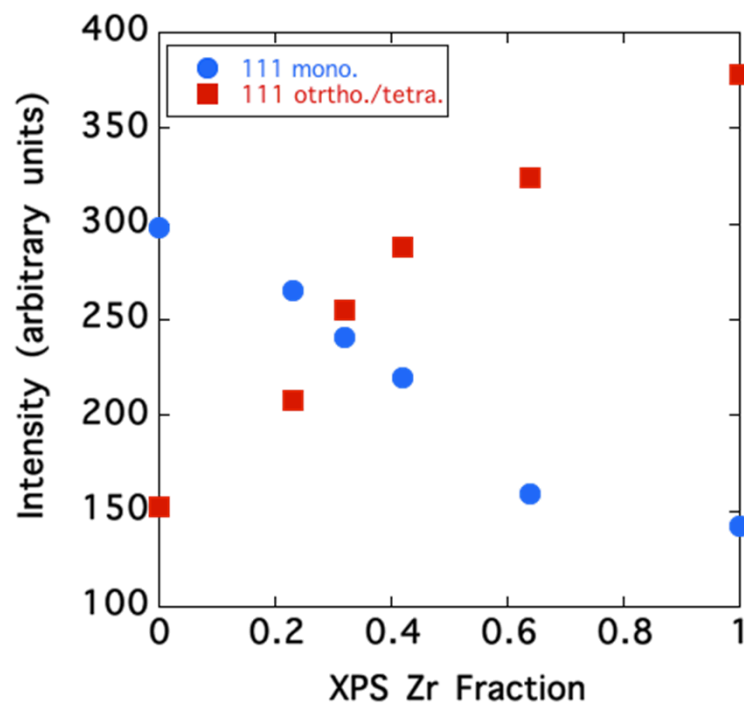


This work – 20 nm HfZrO_2 with TaN electrodes.

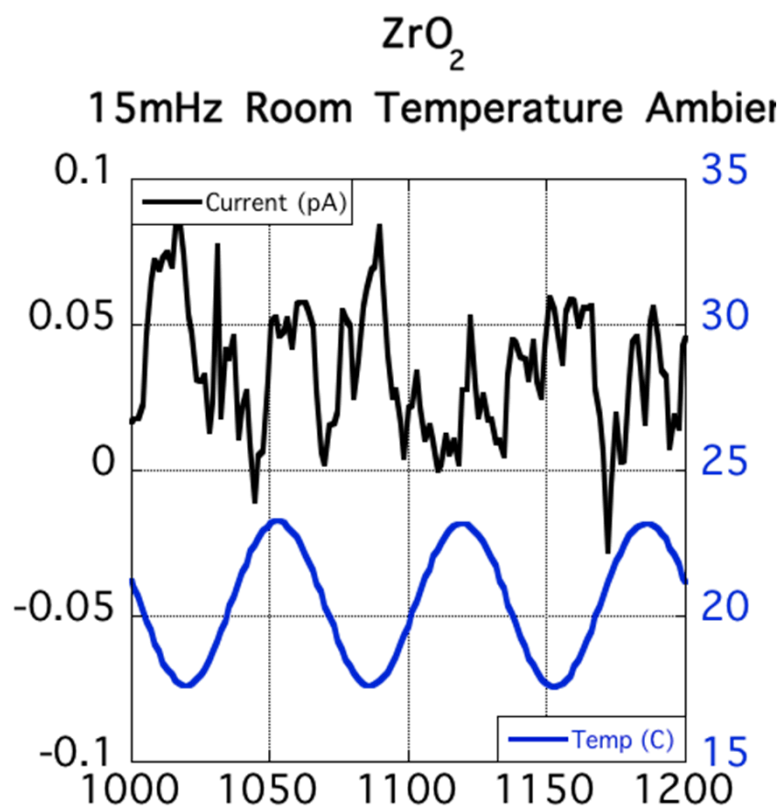


Muller 2012 Nanoletter – 9 nm HfZrO_2 with TiN electrodes.

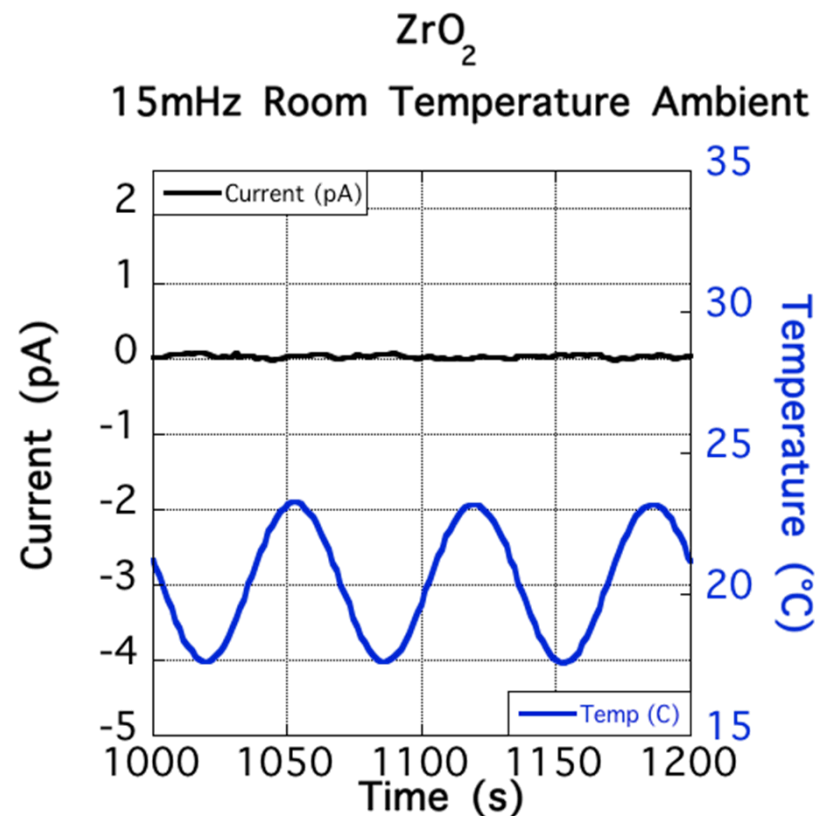
X-ray results



ZrO₂ pyro waveforms zoomed in



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